

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

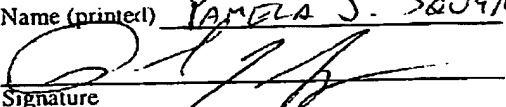
Applicant(s): S. Brad Herner et al.	<b>RECEIVED CENTRAL FAX CENTER MAY 03 2006</b>
Application No.: 10/769,047	
Filed: 1/30/2004	
Title: Low Temperature, Low-Resistivity Heavily Doped P-Type Polysilicon Deposition	
Attorney Docket No.: MA-100-I	
Assistant Commissioner for Patents PO Box 1450 Alexandria VA 22313-1450	May 3, 2006

RESPONSE TO NON-FINAL OFFICE ACTION

This paper is filed in response to the non-final Office Action of February 6, 2006, concerning the above-referenced patent application.

A complete list of pending claims begins on page 2. Amendments to the specification begin on page 5. A discussion of specification amendments appears on page 7. Remarks begin on page 8, and a conclusion appears on page 14.

I hereby certify that this paper is being transmitted by facsimile to the U.S. Patent and Trademark Office on the date shown below.

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App. No. 10/769,047

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